

ABSTRACT OF THE DISCLOSURE

5 A semiconductor device includes: a silicon substrate having a main surface; an interlayer insulation film disposed on the main surface of the silicon substrate and having a top surface and a contact hole reaching the silicon substrate; a conductive film having a side surface and a top surface ranging from the side surface and filling the contact hole; a bottom electrode disposed in contact with the top and side surfaces of the conductive film; a dielectric film disposed on the bottom electrode; and a top electrode disposed on the dielectric film. The conductive film has its top surface more distant
10 from the main surface of the silicon substrate than the interlayer insulation film has its top surface. The semiconductor device can be microfabricated and a desired capacitor structure can also be obtained to provide the semiconductor device with high reliability.